
PF01419B

MOS FET Power Amplifier Module for E-GSM Handy Phone

HITACHI

ADE-208-686 (Z)
1st Edition
Jan. 1, 1999

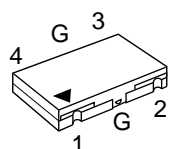
Application

- For E-GSM class4 880 to 915 MHz
- For 3.5 V nominal battery use

Features

- High gain 3stage amplifier : 0 dBm input
- Lead less thin & Small package : 2 mm Max, 0.2cc
- High efficiency : 48% Typ at 35.5 dBm
- Wide gain control range : 70 dB Typ

Pin Arrangement



1 : Pin
2 : V_{apc}
3 : V_{dd}
4 : P_{out}
G : GND

Absolute Maximum Ratings (T_c = 25°C)

Item	Symbol	Rating	Unit
Supply voltage	V _{DD}	8	V
Supply current	I _{DD}	3	A
V _{APC} voltage	V _{APC}	4	V
Input power	P _{in}	10	mW
Operating case temperature	T _c (op)	−30 to +100	°C
Storage temperature	T _{stg}	−30 to +100	°C
Output power	P _{out}	5	W

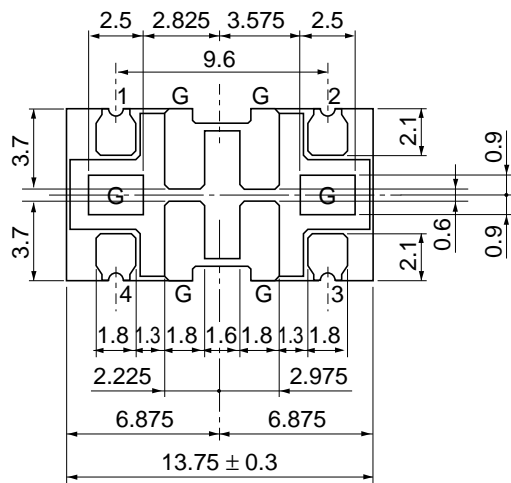
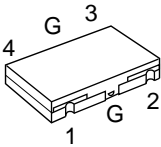
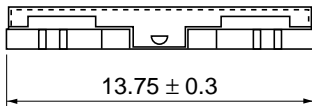
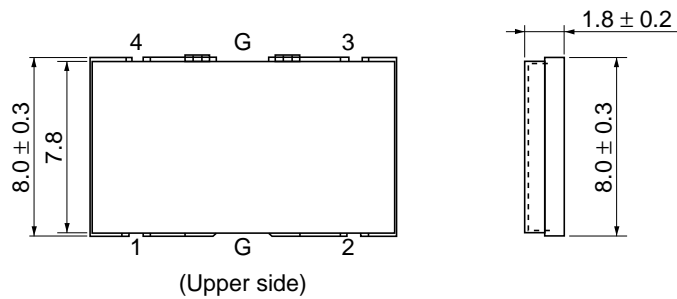
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Electrical Characteristics (Tc = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Frequency range	f	880	—	915	MHz	
Control voltage range	V _{APC}	0.5	—	2.2	V	
Drain cutoff current	I _{DS}	—	—	100	μA	V _{DD} = 8 V, V _{APC} = 0 V
Total efficiency	η _T	43	48	—	%	Pin = 0 dBm, V _{DD} = 3.5 V,
2nd harmonic distortion	2nd H.D.	—	−55	−35	dBc	Pout = 35.5 dBm, Vapc = control
3rd harmonic distortion	3rd H.D.	—	−55	−35	dBc	R _L = R _g = 50 Ω, Tc = 25°C
Input VSWR	VSWR (in)	—	1.5	3	—	
Output power (1)	Pout (1)	35.5	36.0	—	dBm	Pin = 0 dBm, V _{DD} = 3.5 V, V _{APC} = 2.2 V, R _L = R _g = 50 Ω, Tc = 25°C
Output power (2)	Pout (2)	33.5	34.2	—	dBm	Pin = 0 dBm, V _{DD} = 3.0 V, V _{APC} = 2.2 V, R _L = R _g = 50 Ω, Tc = 85°C
Isolation	—	—	−40	−36	dBm	Pin = 0 dBm, V _{DD} = 3.5 V, V _{APC} = 0.5 V, R _L = R _g = 50 Ω, Tc = 25°C
Switching time	tr, tf	—	1	2	μs	Pin = 0 dBm, V _{DD} = 3.5 V, Pout = 0 to 35.5 dBm R _L = R _g = 50 Ω, Tc = 25°C
Stability	—	No parasitic oscillation			—	Pin = 0 dBm, V _{DD} = 3 to 5.1 V, Pout ≤ 35.5 dBm, Vapc ≤ 2.2 V GSM pulse. R _g = 50 Ω, Tc = 25°C, Output VSWR = 6 : 1 All phases
Load VSWR tolerance	—	No degradation			—	Pin = 0 dBm, V _{DD} = 3 to 5.1 V, Pout ≤ 35.5 dBm, Vapc ≤ 2.2 V GSM pulse. R _g = 50 Ω, t = 20 sec., Tc = 25°C, Output VSWR = 10 : 1 All phases

Package Dimensions

Unit: mm



(Bottom side)

Hitachi Code	RF-K01
JEDEC	—
EIAJ	—
Weight (reference value)	—

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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
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For further information write to:

Hitachi Semiconductor
(America) Inc.
2000 Sierra Point Parkway
Brisbane, CA 94005-1897
Tel: <1> (800) 285-1601
Fax: <1> (303) 297-0447

Hitachi Europe GmbH
Electronic components Group
Dornacher StraÙe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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